

TOSHIBA

2SC5411

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

2SC5411

HORIZONTAL DEFLECTION OUTPUT FOR HIGH RESOLUTION DISPLAY, COLOR TV

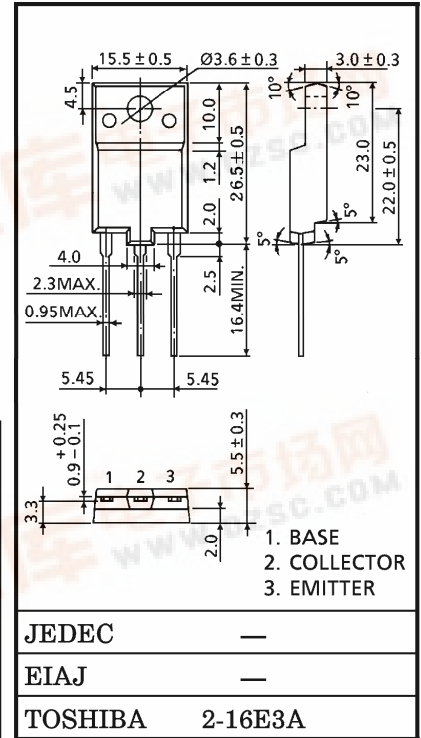
HIGH SPEED SWITCHING APPLICATIONS

- High Voltage : $V_{CB0} = 1500\text{ V}$
- Low Saturation Voltage : $V_{CE(sat)} = 3\text{ V (Max.)}$
- High Speed : $t_f = 0.15\ \mu\text{s (Typ.)}$
- Collector Metal (Fin) is Fully Covered with Mold Resin.

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	1500	V
Collector-Emitter Voltage	V_{CEO}	600	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	DC	I_C	14
	Pulse	I_{CP}	28
Base Current	I_B	7	A
Collector Power Dissipation ($T_c = 25^\circ\text{C}$)	P_C	60	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$

Unit in mm

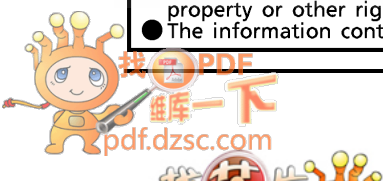


JEDEC	—
EIAJ	—
TOSHIBA	2-16E3A

Weight : 5.5 g (Typ.)

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = 1500 \text{ V}, I_E = 0$	—	—	1	mA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = 5 \text{ V}, I_C = 0$	—	—	10	μA
Emitter-Base Breakdown Voltage		$V_{(BR)CEO}$	$I_C = 10 \text{ mA}, I_B = 0$	600	—	—	V
DC Current Gain		$h_{FE(1)}$	$V_{CE} = 5 \text{ V}, I_C = 2 \text{ A}$	10	—	40	
		$h_{FE(2)}$	$V_{CE} = 5 \text{ V}, I_C = 11 \text{ A}$	4	—	8	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 11 \text{ A}, I_B = 2.75 \text{ A}$	—	—	3	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C = 11 \text{ A}, I_B = 2.75 \text{ A}$	—	1.0	1.5	V
Transition Frequency		f_T	$V_{CE} = 10 \text{ V}, I_C = 0.1 \text{ A}$	—	2	—	MHz
Collector Output Capacitance		C_{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	—	190	—	pF
Switching Time	Storage Time	t_{stg}	$I_{CP} = 8.5 \text{ A}, I_{B1}(\text{end}) = 1.6 \text{ A}$ $f_H = 64 \text{ kHz}$	—	2.5	3.5	μs
	Fall Time	t_f		—	0.15	0.3	



